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rapidly removing at a non-uniform flow rate an upper portion of a semiconductor processing fluid present in said bath while said wafers are in said bath.

7. (twice amended) A method for reducing the contamination on a semiconductor wafer from a wet etching bath comprising:

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processing said semiconductor wafer in said wet etching bath containing an etching fluid;

subsequently rapidly removing at a non-uniform flow rate an upper portion of said etching fluid from said wet etching bath to remove contaminants from the surface of said wet etching bath while retaining said semiconductor wafer in said wet etching bath; and

subsequently removing said semiconductor wafer from said wet etching bath.

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11. (twice amended) A [The] method for removing contaminants from a semiconductor processing bath for processing semiconductor wafers, said method comprising rapidly removing an upper portion of a semiconductor processing fluid present in said bath, while said wafers are in said bath, [according to claim 9, wherein said upper portion of said etching fluid is removed] by opening a valve in said [wet etching] bath.

12. (twice amended) A [The] method for removing contaminants from a semiconductor processing bath for processing semiconductor wafers, said method comprising rapidly removing an upper portion of a semiconductor processing fluid present in said bath, while said wafers are in said bath, [according to claim 9, wherein said upper portion of said etching fluid is removed] by hingedly releasing a door located at an upper portion of said [wet etching] bath.

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13. (twice amended) A [The] method for removing contaminants from a semiconductor processing bath for processing semiconductor wafers, said method comprising rapidly removing an upper portion of a semiconductor processing fluid present in said bath, while said wafers are in said bath, [according to claim 9, wherein said upper portion of said etching fluid is removed] by sliding a door located at an upper portion of said [wet etching] bath.

Subj

14. (twice amended) A [The] method for removing contaminants from a semiconductor processing bath for processing semiconductor wafers, said method comprising rapidly removing an upper portion of a semiconductor processing fluid present in said bath, while said wafers are in said bath, [according to claim 9, wherein said upper portion of said etching fluid is removed] by rapidly removing a wafer boat containing said semiconductor wafer from said [wet etching] bath.

15. (twice amended) A The method for removing contaminants from a semiconductor processing bath for processing semiconductor wafers, said method comprising rapidly removing an upper portion of a semiconductor processing fluid present in said bath, while said wafers are in said bath, [according to claim 9, wherein said upper portion of said etching fluid is removed] by telescopically collapsing sidewalls of a vessel containing said [wet etching] bath.

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17. (twice amended) A method for etching a semiconductor wafer, said method comprising:

placing an etching fluid into a wet etching vessel;

placing said semiconductor wafer in said etching fluid;

contacting said semiconductor wafer with said etching fluid for a predetermined time;

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rapidly removing a portion of said etching fluid from the upper surface of said wet etching vessel at a non-uniform flow rate while keeping said semiconductor wafer immersed in said etching fluid; and[,]

removing said semiconductor wafer from said etching fluid.

21. (twice amended) A [The] method for etching a semiconductor wafer, said method comprising:

placing an etching fluid into a wet etching vessel;

placing said semiconductor wafer in said etching fluid;

contacting said semiconductor wafer with said etching fluid for a predetermined time; and

rapidly removing a portion of said etching fluid from the upper surface of said wet etching vessel [according to claim 20, wherein said top portion of said etching fluid is removed] by opening a valve in said wet etching vessel.

22. (twice amended) A [The] method for etching a semiconductor wafer, said method comprising:

placing an etching fluid into a wet etching vessel;

placing said semiconductor wafer in said etching fluid;

contacting said semiconductor wafer with said etching fluid for a predetermined time; and

rapidly removing a portion of said etching fluid from the upper surface of said wet etching vessel [according to claim 20, wherein said top portion of said etching fluid is

removed] by hingedly releasing a door located at an upper portion of said wet etching vessel.

23. (twice amended) A [The] method for etching a semiconductor wafer, said method comprising:

placing an etching fluid into a wet etching vessel;

placing said semiconductor wafer in said etching fluid;

contacting said semiconductor wafer with said etching fluid for a predetermined time; and

rapidly removing a portion of said etching fluid from the upper surface of said wet etching vessel [according to claim 20, wherein said top portion of said etching fluid is removed] by sliding a door located at an upper portion of said wet etching vessel.

24. (twice amended) A [The] method for etching a semiconductor wafer, said method comprising:

placing an etching fluid into a wet etching vessel;

placing said semiconductor wafer in said etching fluid;

contacting said semiconductor wafer with said etching fluid for a predetermined time; and

rapidly removing a portion of said etching fluid from the upper surface of said wet etching vessel [according to claim 20, wherein said top portion of said etching fluid is removed] by rapidly removing a wafer boat containing said semiconductor wafers from said wet etching vessel.

SUB D
25. (twice amended) A [The] method for etching a semiconductor wafer, said method comprising:

placing an etching fluid into a wet etching vessel;

placing said semiconductor wafer in said etching fluid;

contacting said semiconductor wafer with said etching fluid for a predetermined time; and

rapidly removing a portion of said etching fluid from the upper surface of said wet etching vessel at a non-constant velocity [according to claim 20, wherein said top portion of said etching fluid is removed by telescopically collapsing sidewalls of said wet etching vessel.

SUB D
44. (twice amended) A method for reducing the contaminants on a silicon wafer during a wet etching process, said method comprising:

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immersing a wafer boat in an etching vessel having an etching fluid therein for a sufficient time to etch said silicon wafer; and

rapidly removing said wafer boat from said etching vessel to remove contaminants residing on the upper surface of said etching fluid by causing said etching fluid to spill out of said vessel at a non-uniform flow rate.